

## SWITCHING REGULATOR APPLICATIONS

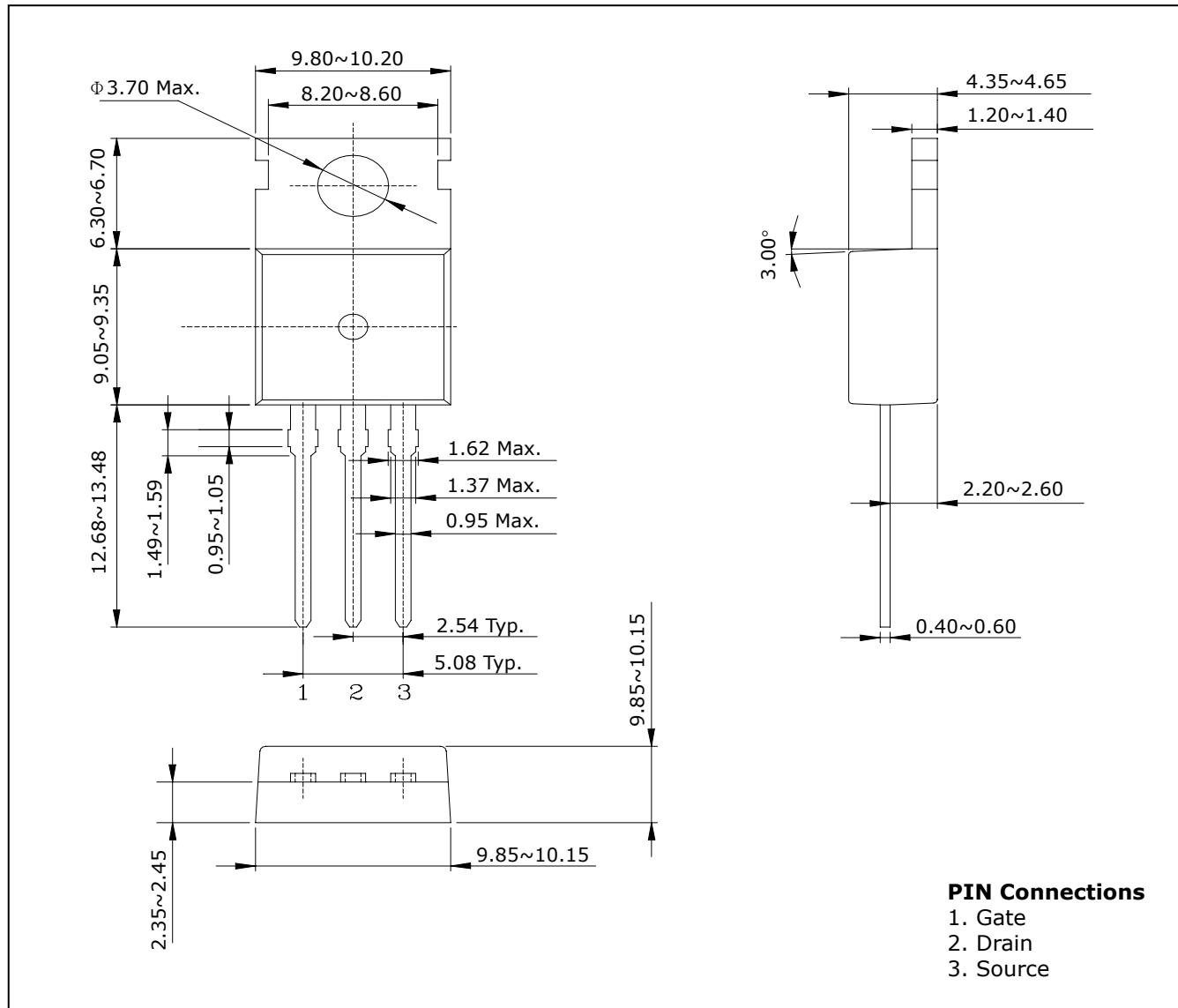
### Features

- High Voltage:  $BV_{DSS}=600V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=7.5\text{pF}$ (Typ.)
- Low gate charge :  $Q_g=16\text{nC}$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=2.5\Omega$ (Max.)

### Ordering Information

Type NO.	Marking	Package Code
STK0460P	STK0460	TO-220AB-3L

### Outline Dimensions

**unit : mm**


**Absolute maximum ratings**

(Tc=25°C)

<b>Characteristic</b>	<b>Symbol</b>	<b>Rating</b>	<b>Unit</b>
Drain-source voltage	V <sub>DSS</sub>	600	V
Gate-source voltage	V <sub>GSS</sub>	±30	V
Drain current (DC)	I <sub>D</sub>	(Tc=25°C)	4
		(Tc=100°C)	2.2
Drain current (Pulsed) *	I <sub>DM</sub>	16	A
Drain Power dissipation	P <sub>D</sub>	45	W
Avalanche current (Single) ②	I <sub>AS</sub>	4	A
Single pulsed avalanche energy ②	E <sub>AS</sub>	150	mJ
Avalanche current (Repetitive) ①	I <sub>AR</sub>	4	A
Repetitive avalanche energy ①	E <sub>AR</sub>	7	mJ
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	

\* Limited by maximum junction temperature

<b>Characteristic</b>	<b>Symbol</b>	<b>Typ.</b>	<b>Max</b>	<b>Unit</b>
Thermal resistance	R <sub>th(J-C)</sub>	-	2.8	°C/W
	R <sub>th(J-a)</sub>	-	83.3	

## Electrical Characteristics

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0	600	-	-	V
Gate-threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub>	2.0	-	4.0	V
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
Drain-Source on-resistance ④	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2.0A	-	1.9	2.5	Ω
Forward transfer admittance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.0A	-	3.0	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	-	520	780	pF
Output capacitance	C <sub>oss</sub>		-	35	53	
Reverse transfer capacitance	C <sub>rss</sub>		-	7.5	12	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =300V, I <sub>D</sub> =4A R <sub>G</sub> =25Ω	-	10	-	ns
Rise time	t <sub>r</sub>		-	42	-	
Turn-off delay time	t <sub>d(off)</sub>		-	38	-	
Fall time	t <sub>f</sub>		-	46	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =300V, V <sub>GS</sub> =10V I <sub>D</sub> =4A	-	16	24	nC
Gate-source charge	Q <sub>gs</sub>		-	2.8	4.2	
Gate-drain charge	Q <sub>gd</sub>		-	5.5	8.3	

## Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

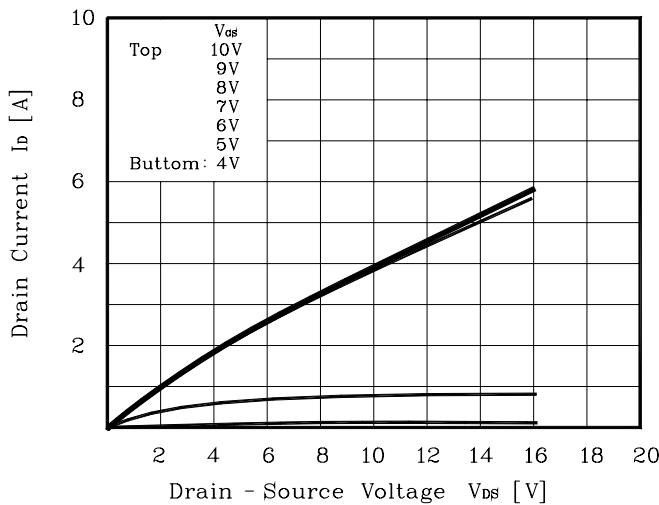
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous source current	I <sub>S</sub>	Integral reverse diode in the MOSFET	-	-	4	A
Source current (Pulsed) ①	I <sub>SM</sub>		-	-	16	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =4A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>s</sub> =4A di <sub>s</sub> /dt=100A/us	-	310	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	2.26	-	uC

Note :

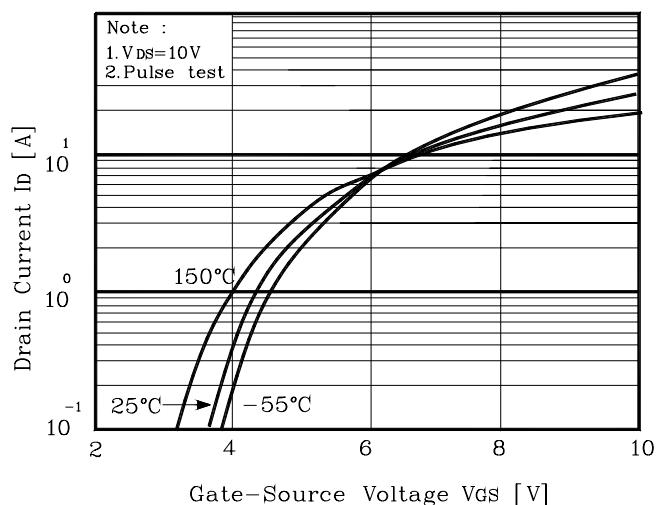
- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=17mH, I<sub>AS</sub>=4A, V<sub>DD</sub>=50V, R<sub>G</sub>=27Ω
- ③ Pulse Test : Pulse Width < 300us, Duty cycle≤ 2%
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

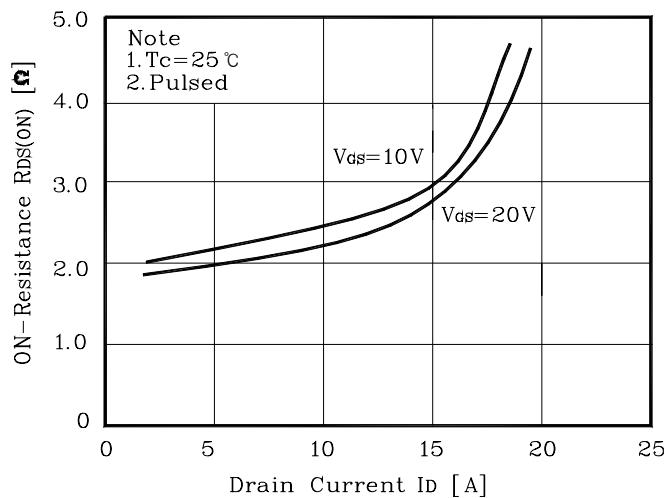
**Fig. 1  $I_D$  -  $V_{DS}$**



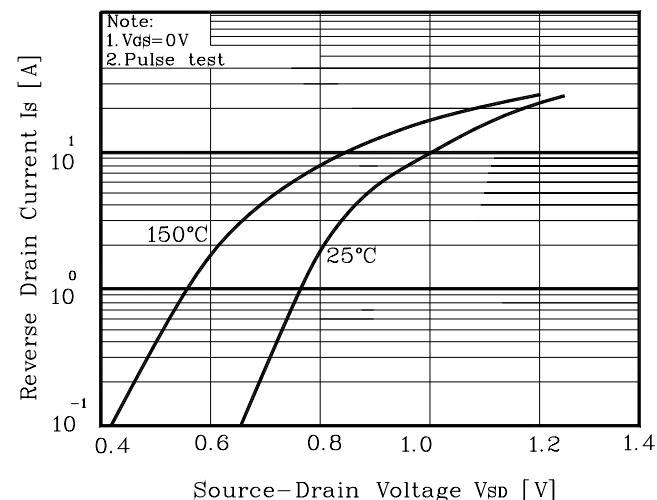
**Fig. 2  $I_D$  -  $V_{GS}$**



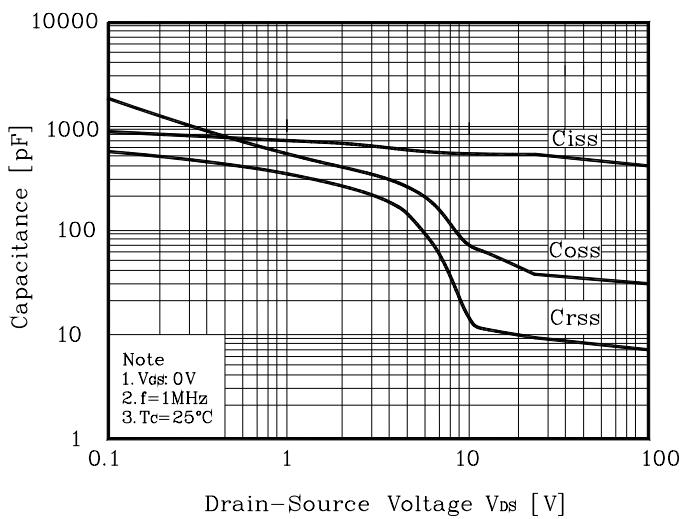
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



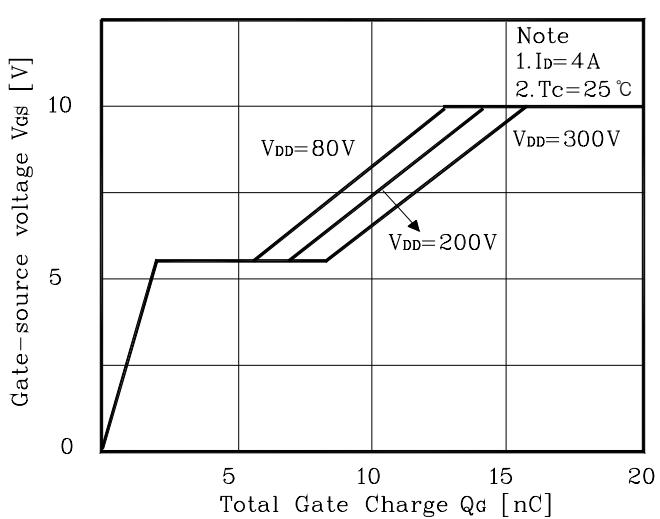
**Fig. 4  $I_S$  -  $V_{SD}$**



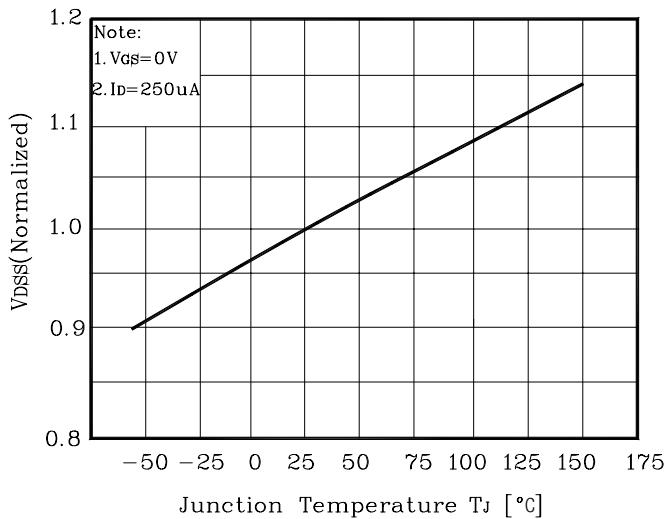
**Fig. 5 Capacitance -  $V_{DS}$**



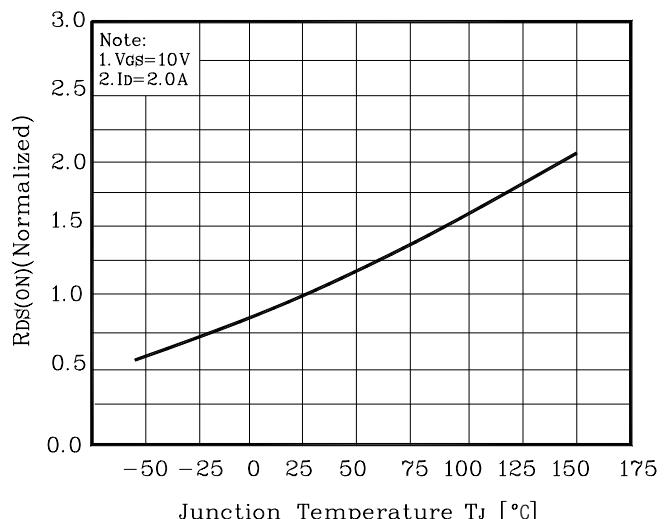
**Fig. 6  $V_{GS}$  -  $Q_G$**



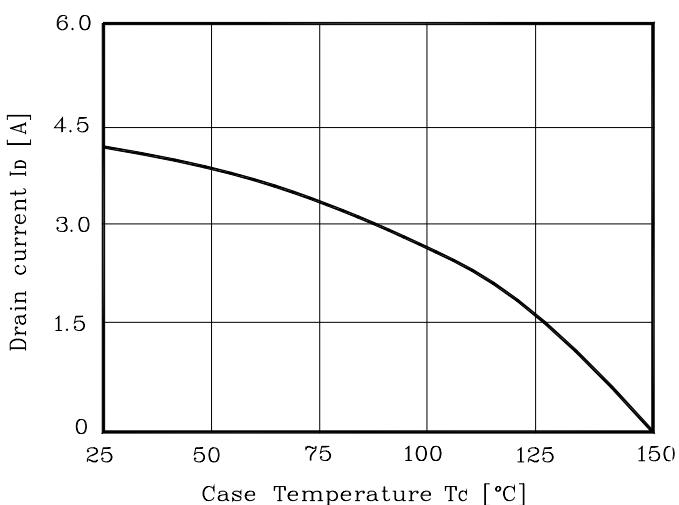
**Fig. 7  $V_{DSS}$  -  $T_J$**



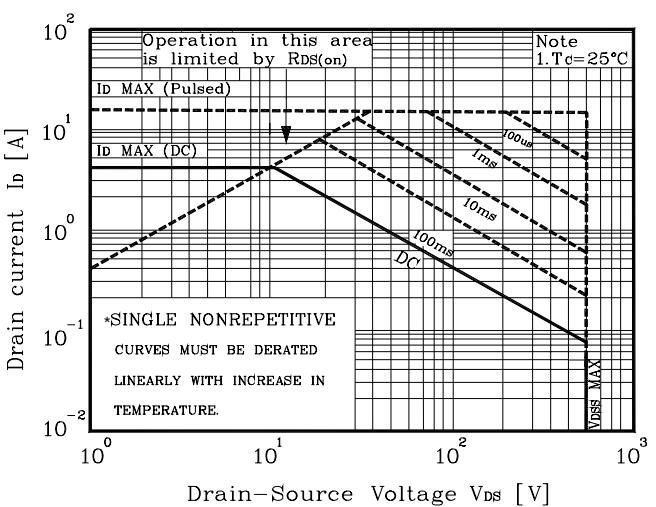
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



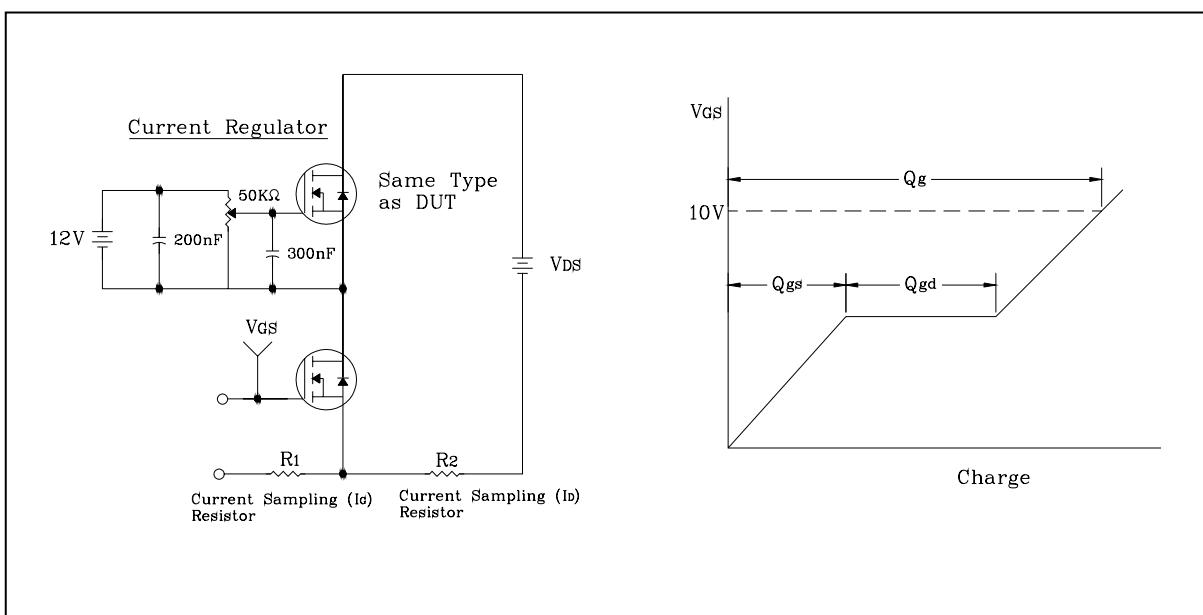
**Fig. 9  $I_D$  -  $T_C$**



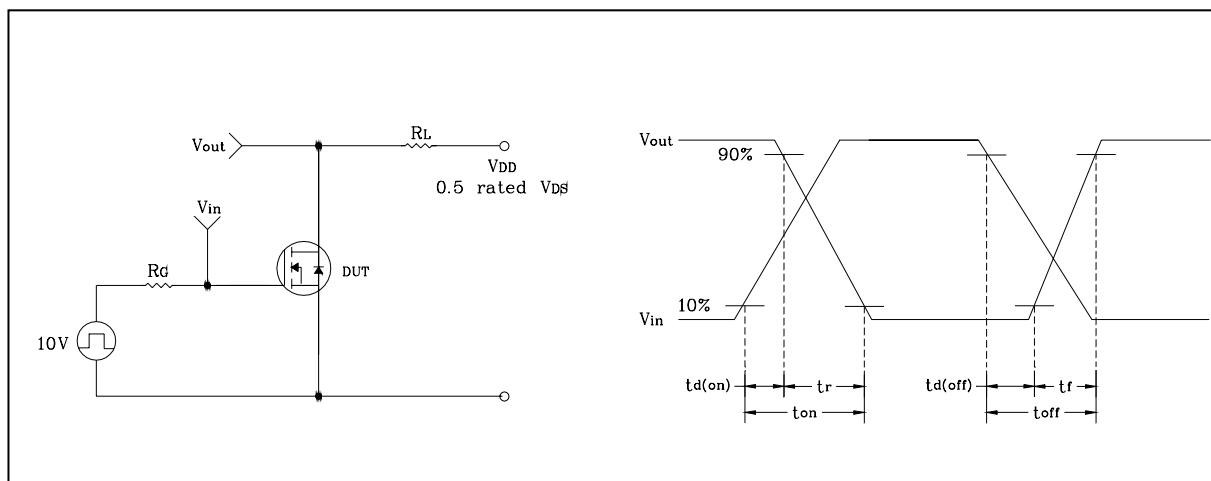
**Fig. 10 Safe Operating Area**



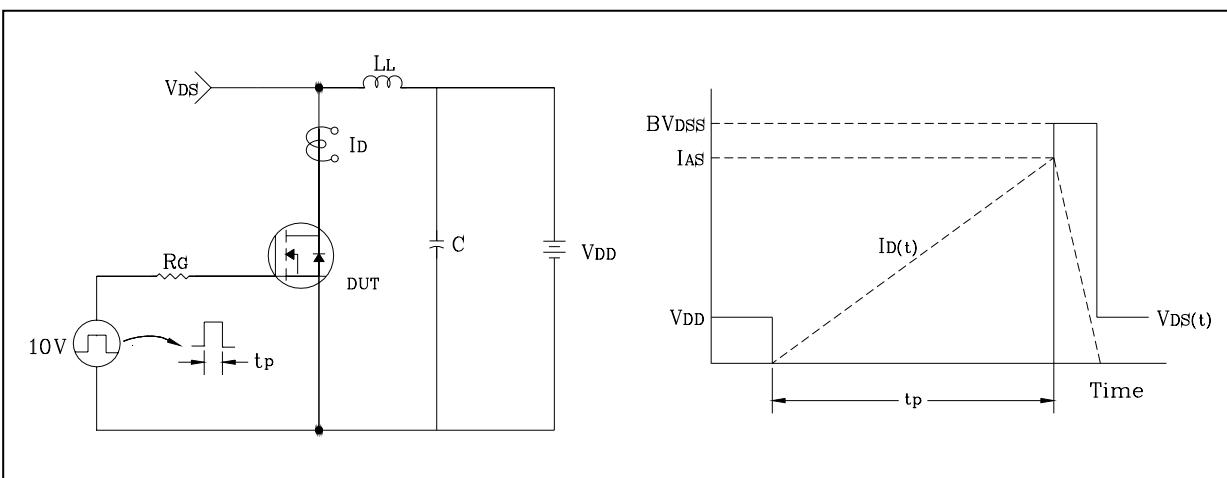
**Fig. 11 Gate Charge Test Circuit & Waveform**



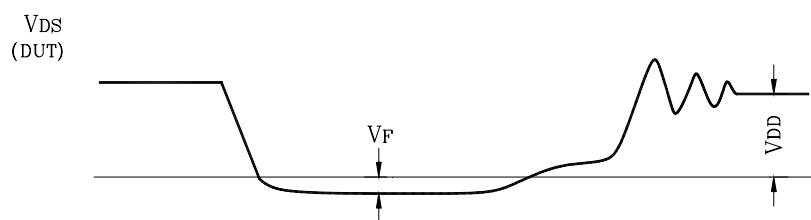
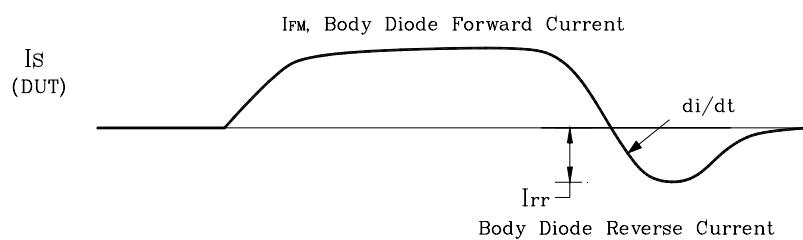
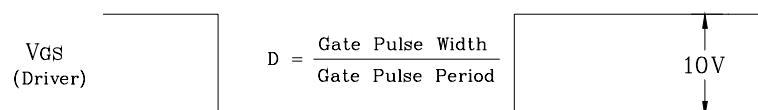
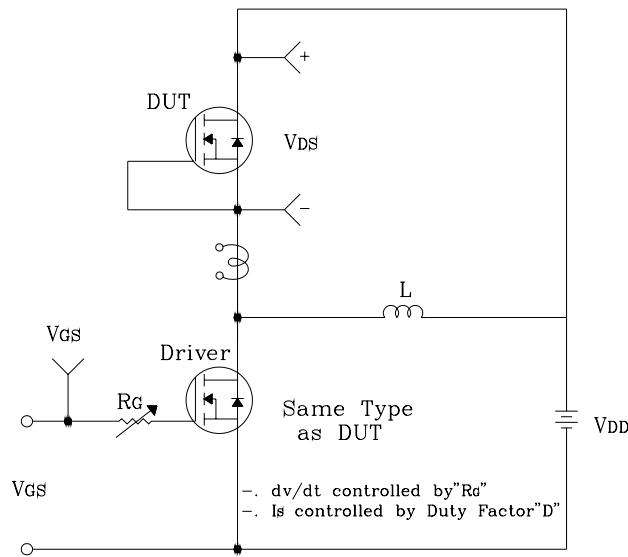
**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**



**Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**



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